Discrete POWER & Signal Technologies



NPN General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 10. See PN100A for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

| Symbol | Parameter | Value | Units |
|------------------|--|-------------|-------|
| V _{CEO} | Collector-Emitter Voltage | 25 | V |
| V _{CBO} | Collector-Base Voltage | 25 | V |
| V _{EBO} | Emitter-Base Voltage | 5.0 | V |
| I _C | Collector Current - Continuous | 500 | mA |
| TJ, Tsta | Operating and Storage Junction Temperature Range | -55 to +150 | ۰C |

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

| Symbol | Characteristic | Max | Units |
|------------------|---|-------------------------------|-------|
| | | 2N3390 / 3391/A / 3392 / 3393 | |
| P _D | Total Device Dissipation | 625 | mW |
| | Derate above 25°C | 5.0 | mW/°C |
| R _{θJC} | Thermal Resistance, Junction to Case | 83.3 | °C/W |
| R _{0JA} | Thermal Resistance, Junction to Ambient | 200 | °C/W |

NPN General Purpose Amplifier (continued)

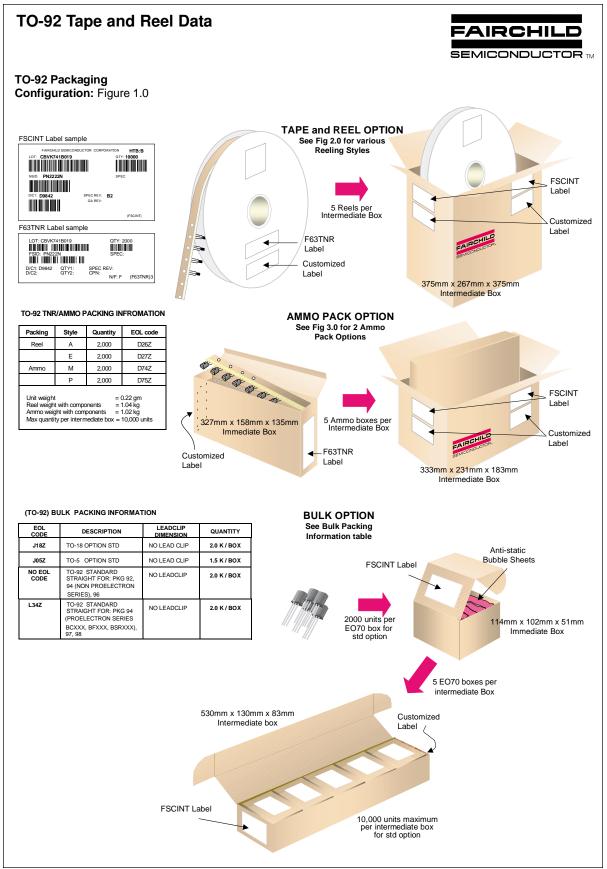
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|---|---|-----|----|---|----|
| | | | | | |

| Symbol | Parameter | Test Conditions | Min | Max | Units |
|----------------------|--|--|-----|-----|-------|
| | | | | | |
| OFF CHA | ARACTERISTICS | | | | |
| V _{(BR)CEO} | Collector-Emitter Breakdown I _C = 10 mA, I _B = 0 Voltage* | | 25 | | V |
| V _{(BR)CBO} | Collector-Base Breakdown Voltage | $I_{C} = 10 \ \mu A, I_{E} = 0$ | 25 | | V |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage | $I_E = 10 \ \mu A, \ I_C = 0$ | 5.0 | | V |
| I _{CBO} | Collector-Cutoff Current | $V_{CB} = 18 \text{ V}, I_E = 0$ | | 100 | nA |
| I _{EBO} | Emitter-Cutoff Current | $V_{EB} = 5.0 \text{ V}, I_{C} = 0$ | | 100 | nA |
| ON CHAI | RACTERISTICS* | V _{CE} = 4.5 V, I _C = 2.0 mA | | | |

SMALL SIGNAL CHARACTERISTICS

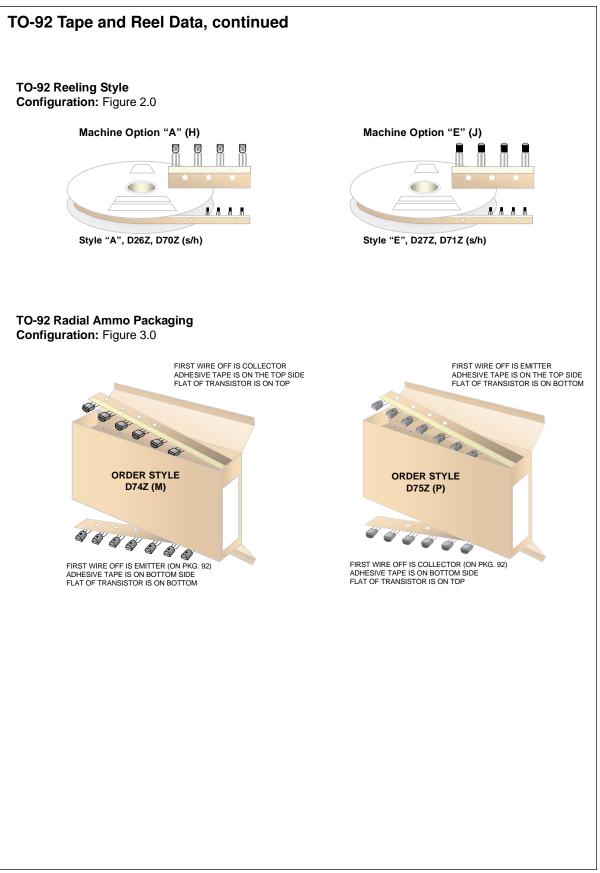
| C _{ob} | Output Capacitance | V _{CB} = 10 V, f = 1.0 MHz | 2.0 | 10 | pF |
|-----------------|---------------------------|--|-------------------------|---------------------------|----|
| h _{fe} | Small-Signal Current Gain | $\label{eq:loss} \begin{array}{l} I_{C} = 2.0 \text{ mA}, \ V_{CE} = 4.5 \text{ V}, \\ f = 1.0 \text{ kHz} & \textbf{2N3390} \\ & \textbf{2N3391/A} \\ & \textbf{2N3392} \\ & \textbf{2N3393} \end{array}$ | 400 250 150 90 | 1250 800 500 400 | |
| NF | Noise Figure | | | 5.0 | dB |

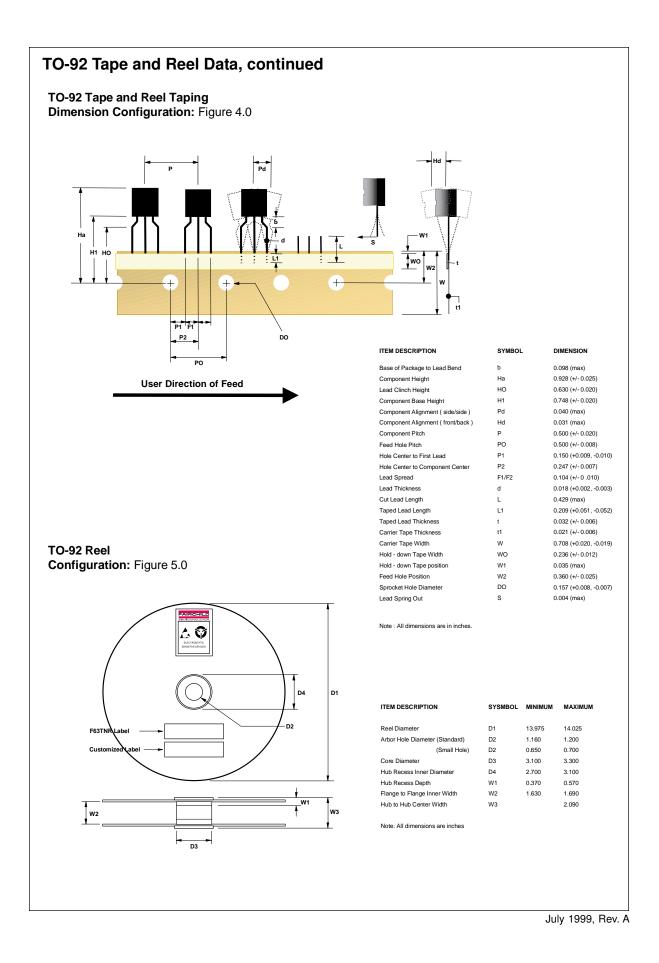
*Pulse Test: Pulse Width $\leq 300~\mu\text{s},~\text{Duty}~\text{Cycle} \leq 2.0\%$

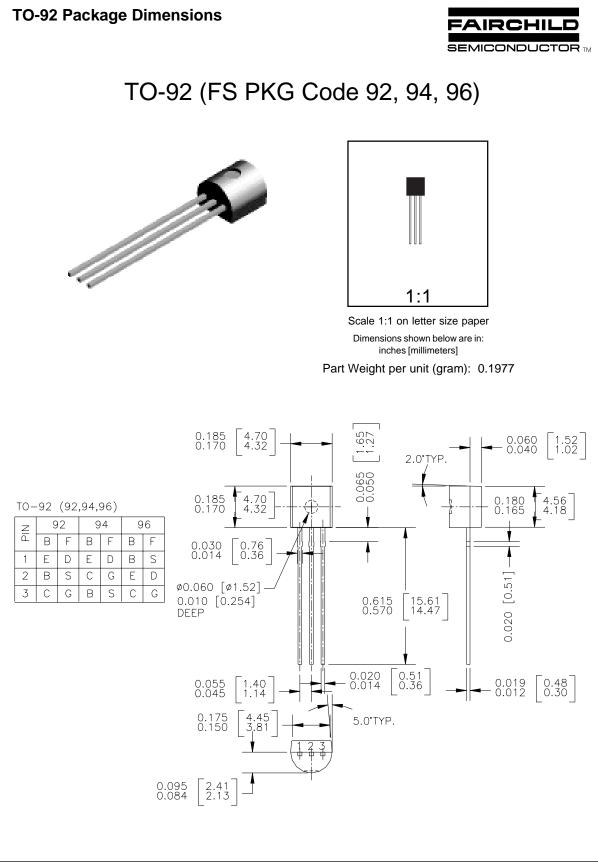


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|--------------------------|---------------------------|---|
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